

제23회 한국반도체학술대회

2016년 2월 22일(월)-24일(수), 강원도 하이원리조트

D. Thin Film Process Technology 분과

Room B

태백II+III(5층)

2016년 2월 24일(수) 10:10-11:40

[WB2-D] Thin Films for Emerging Devices II

좌장 : 전상훈(고려대학교), 최창환(한양대학교)

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| WB2-D-1 | 10:10-10:25 | Low-Temperature P-Type Poly-Ge Thin-Film Transistor Fabricated by Metal-Induced Lateral Crystallization for High Hole Mobility
Jae Hyo Park ¹ , Yoonyoung Bae ² , Seung Ki Joo ¹ , and Donghwan Ahn ²
<i>¹Department of Material Science and Engineering, Research Institute of Advanced Materials, Seoul National University; ²Department of Advanced Materials Engineering, Kookmin University</i> |
| WB2-D-2 | 10:25-10:40 | Wearable Transparent Oxide Thin-Film Transistor Via Inorganic-Based Laser Lift-Off
Han Eol Lee and Keon Jae Lee
<i>Department of Materials Science and Engineering, KAIST</i> |
| WB2-D-3 | 10:40-10:55 | Atomic Layer Deposition of GeTe and GexSbyTez Alloys Using Ge(N((CH₃)₃Si)₂)₂ Precursor
Taehong Gwon ¹ , Taeyong Eom ¹ , Sijung Yoo ¹ , Eui-sang Park ¹ , Sanggyun Kim ¹ , Moo-sung Kim ² , Iain Buchanan ³ , Manchao Xiao ³ , Sergei Ivanov ³ , and Cheol Seong Hwang ¹
<i>¹Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, ²Air Products Korea, ³Air Products and Chemicals, Inc.</i> |
| WB2-D-4 | 10:55-11:10 | Decreasing Interfacial Layers of The Ferroelectric Hf_{0.5}Zr_{0.5}O₂ Film Capacitors by Wake-Up Effect
Han Joon Kim, Min Hyuk Park, Yu Jin Kim, Taehwan Moon, Keum Do Kim, Young Hwan Lee, Seung Dam Hyun, and Cheol Seong Hwang
<i>Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University</i> |
| WB2-D-5 | 11:10-11:25 | Transparent Poly-Si Gate Thin-Film Transistors by NiSi₂ Seed-Induced Lateral Crystallization for Display Applications.
Ji Su Han, Jae Hyo Park, Hyung Yoon Kim, Ki Hwan Seok, Zohreh Kiaee, and Seung Ki Joo
<i>Department of Material Science and Engineering, Research Institute of Advanced Materials, Seoul National University</i> |
| WB2-D-6 | 11:25-11:40 | A New Method To Form NiGeSn Layer To Reduce Contact Resistance in Source/Drain Region for Future Ge CMOSFET
Jeyoung Kim ¹ , Meng Li ¹ , Jungwoo Oh ² , and Hi-Deok Lee ¹
<i>¹Department of Electronics Engineering, Chungnam National University, ²School of Integrated Technology, Yonsei University</i> |